



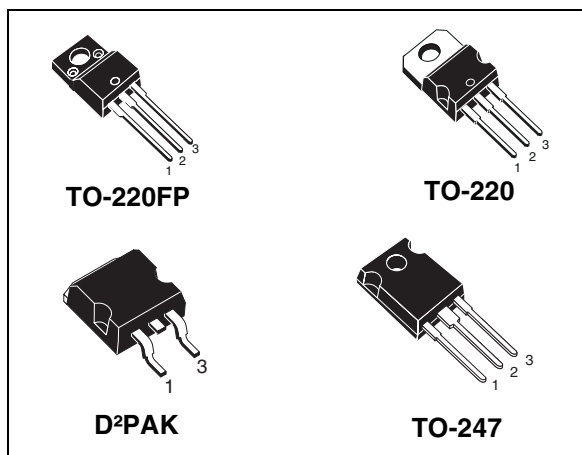
STB28NM50N, STF28NM50N STP28NM50N, STW28NM50N

N-channel 500 V, 0.135 Ω , 21 A D²PAK, TO-220, TO-220FP, TO-247
MDmesh™ II Power MOSFET

Features

Order codes	V _{DSS} (@T _{Jmax})	R _{DS(on)} max.	I _D
STB28NM50N	550 V	< 0.158 Ω	21 A
STF28NM50N			
STP28NM50N			
STW28NM50N			

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



Applications

- Switching applications

Description

These devices are N-channel Power MOSFETs developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram

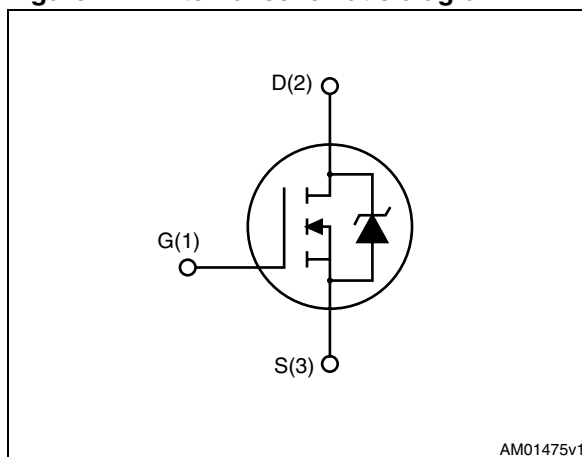


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB28NM50N	28NM50N	D ² PAK	Tape and reel
STF28NM50N		TO-220FP	Tube
STP28NM50N		TO-220	
STW28NM50N		TO-247	

Contents

1 **Electrical ratings** 3

2 **Electrical characteristics** 4

 2.1 Electrical characteristics (curves) 6

3 **Test circuits** 9

4 **Package mechanical data** 10

5 **Packaging mechanical data** 18

6 **Revision history** 20



1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-247	TO-220FP	
V _{DS}	Drain-source voltage (V _{GS} = 0)	500				V
V _{GS}	Gate- source voltage	± 25				V
I _D	Drain current (continuous) at T _C = 25 °C	21			21 ⁽¹⁾	A
I _D	Drain current (continuous) at T _C = 100 °C	13			13 ⁽¹⁾	A
I _{DM} ⁽²⁾	Drain current (pulsed)	84			84 ⁽¹⁾	A
P _{TOT}	Total dissipation at T _C = 25 °C	150			35	W
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t=1 s;T _C =25 °C)				2500	V
dv/dt ⁽³⁾	Peak diode recovery voltage slope	15				V/ns
T _{stg}	Storage temperature	- 55 to 150				°C
T _j	Max. operating junction temperature	150				°C

1. Limited only by maximum temperature allowed

2. Pulse width limited by safe operating area

3. $I_{SD} \leq 21\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS\text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value				Unit
		TO-220	D ² PAK	TO-247	TO-220FP	
$R_{thj-case}$	Thermal resistance junction-case max	0.83			3.6	$^{\circ}\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max	62.5		50	62.5	$^{\circ}\text{C}/\text{W}$
$R_{thj-pcb}$ ⁽¹⁾	Thermal resistance junction-pcb max		30			$^{\circ}\text{C}/\text{W}$
T_I	Maximum lead temperature for soldering purpose	300		300		$^{\circ}\text{C}$

1. When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by $T_j\text{ Max}$)	7.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^{\circ}\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	300	mJ

2 Electrical characteristics

($T_{CASE}=25^{\circ}\text{C}$ unless otherwise specified)

Table 5. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	500			V
I_{DSS}	Zero gate voltage drain current ($V_{GS} = 0$)	$V_{DS} = \text{max rating}$ $V_{DS} = \text{max rating}$, @ 125°C			1 100	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 25 \text{ V}$			100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}$, $I_D = 10.5 \text{ A}$		0.135	0.158	Ω

Table 6. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	$V_{DS} = 25 \text{ V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$	-	1735 122 4.3	-	pF pF pF
$C_{oss(eq)}^{(1)}$	Equivalent output capacitance time related	$V_{GS} = 0$, $V_{DS} = 0 \text{ to } 50 \text{ V}$	-	418	-	pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 400 \text{ V}$, $I_D = 21 \text{ A}$, $V_{GS} = 10 \text{ V}$, (see Figure 19)	-	50 9.5 25	-	nC nC nC
R_g	Gate input resistance	$f=1 \text{ MHz}$ Gate DC Bias=0 Test signal level=20 mV open drain	-	2.7	-	Ω

1. $C_{oss(eq)}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 7. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 250\text{ V}$, $I_D = 10.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see Figure 18)	-	13.6	-	ns
t_r	Rise time			19		ns
$t_{d(off)}$	Turn-off delay time			62		ns
t_f	Fall time			52		ns

Table 8. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		21	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				84	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 21\text{ A}$, $V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$ (see Figure 23)	-	326		ns
Q_{rr}	Reverse recovery charge			5		μC
I_{RRM}	Reverse recovery current			30		A
t_{rr}	Reverse recovery time	$I_{SD} = 21\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 400\text{ V}$, $T_J = 150\text{ }^\circ\text{C}$ (see Figure 23)	-	376		ns
Q_{rr}	Reverse recovery charge			6.2		μC
I_{RRM}	Reverse recovery current			33.2		A

1. Pulse width limited by safe operating area

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220, D²PAK

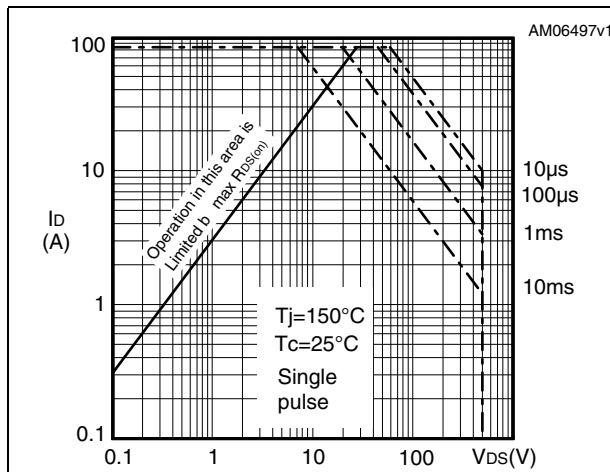


Figure 3. Thermal impedance for TO-220, D²PAK

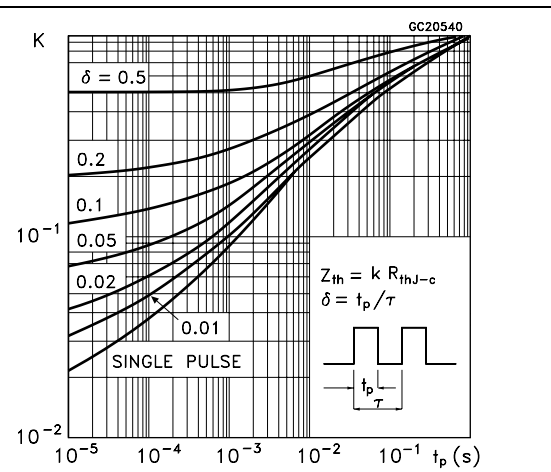


Figure 4. Safe operating area for TO-220FP

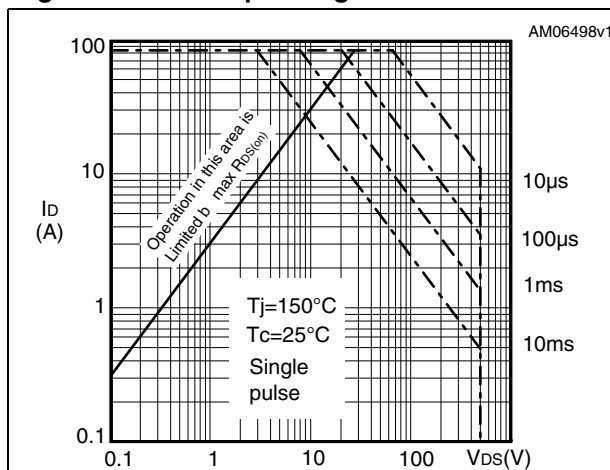


Figure 5. Thermal impedance for TO-220FP

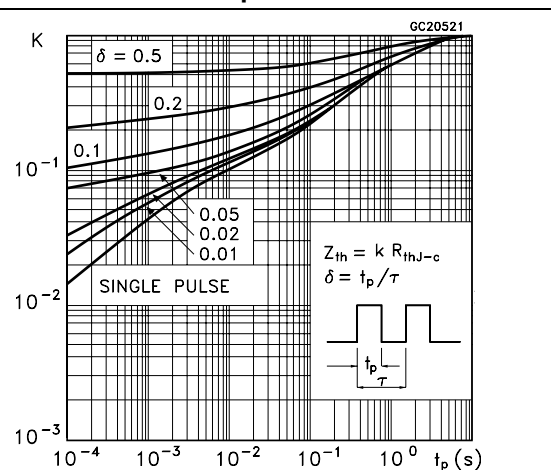


Figure 6. Safe operating area for TO-247

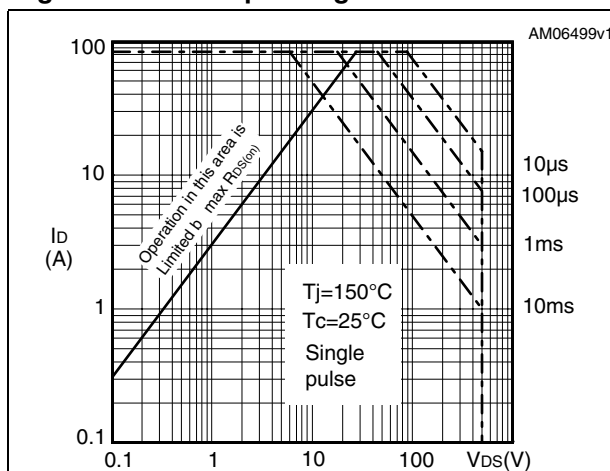


Figure 7. Thermal impedance for TO-247

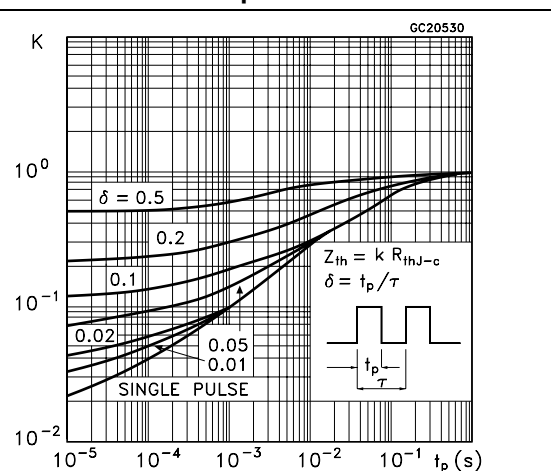


Figure 8. Output characteristics

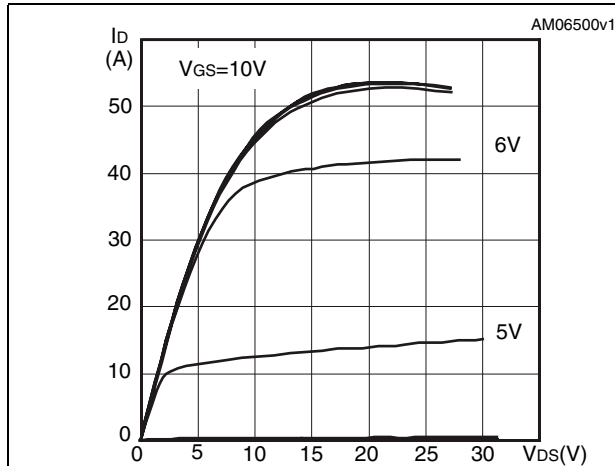


Figure 9. Transfer characteristics

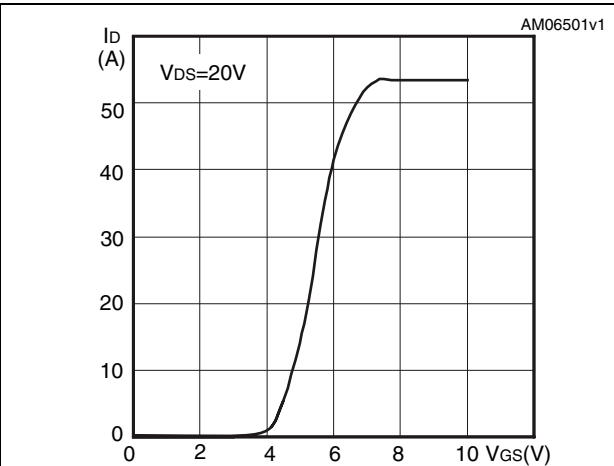


Figure 10. Gate charge vs gate-source voltage

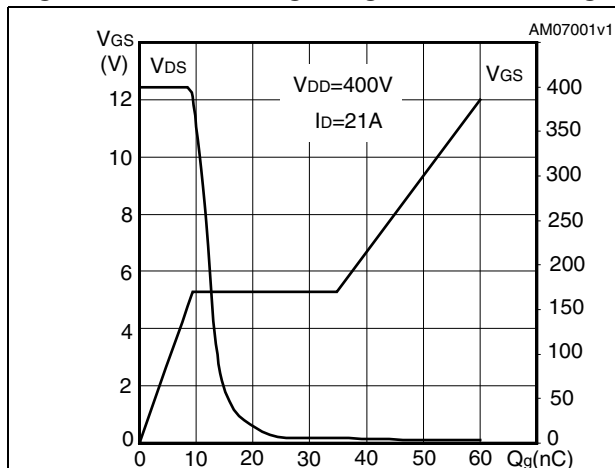


Figure 11. Static drain-source on resistance

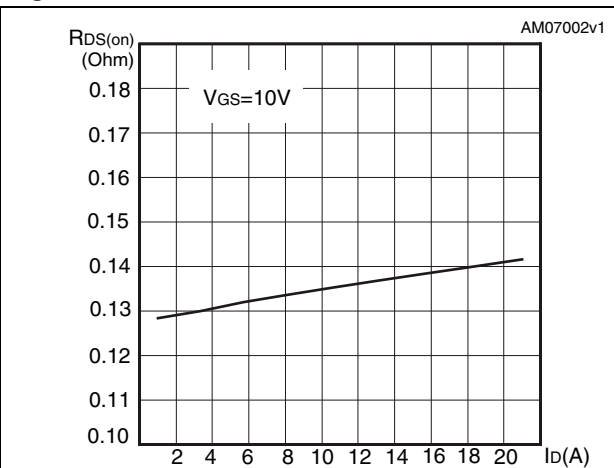


Figure 12. Capacitance variations

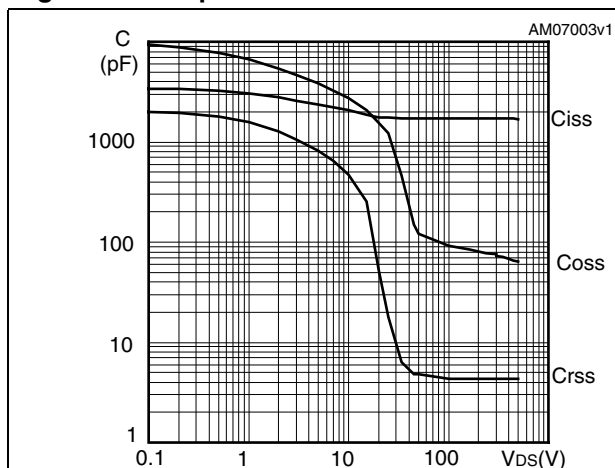


Figure 13. Output capacitance stored energy

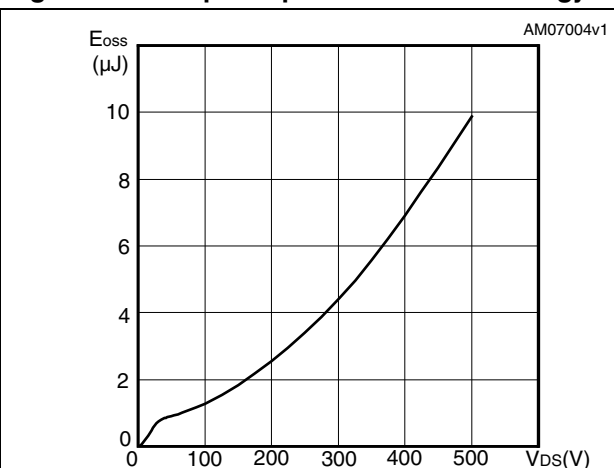


Figure 14. Normalized gate threshold voltage vs temperature

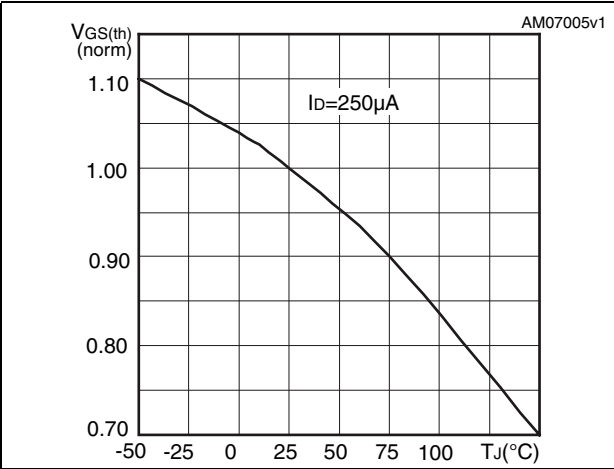


Figure 15. Normalized on resistance vs temperature

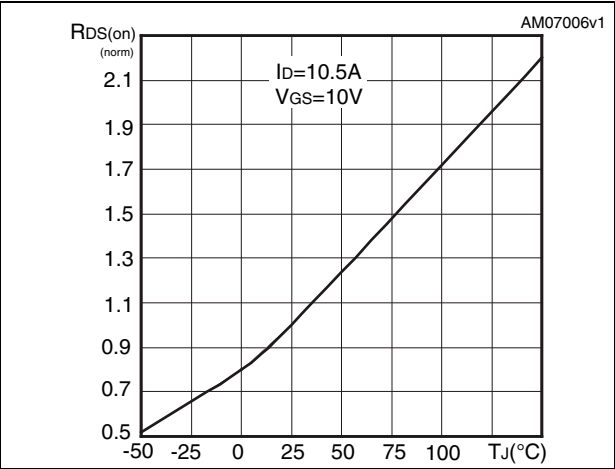


Figure 16. Normalized B_{VDSS} vs temperature

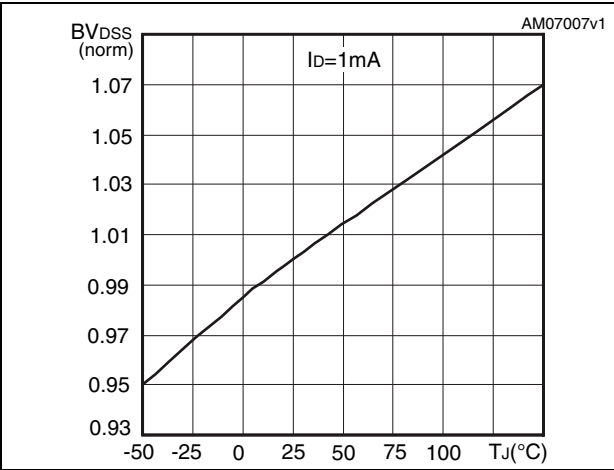
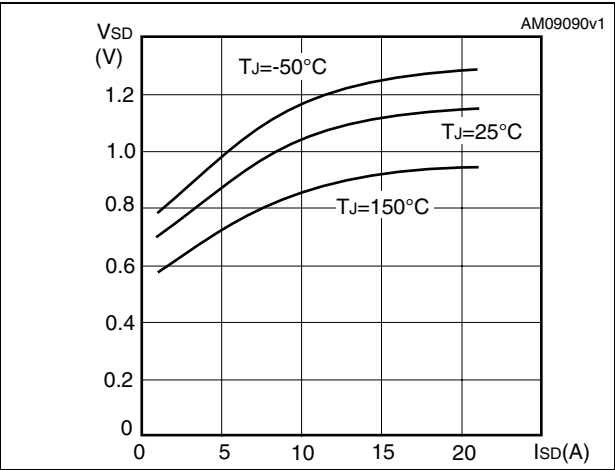


Figure 17. Source-drain diode forward characteristics



3 Test circuits

Figure 18. Switching times test circuit for resistive load



Figure 19. Gate charge test circuit



Figure 20. Test circuit for inductive load switching and diode recovery times



Figure 21. Unclamped inductive load test circuit



Figure 22. Unclamped inductive waveform



Figure 23. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 9. TO-220FP mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

Figure 24. TO-220FP drawing

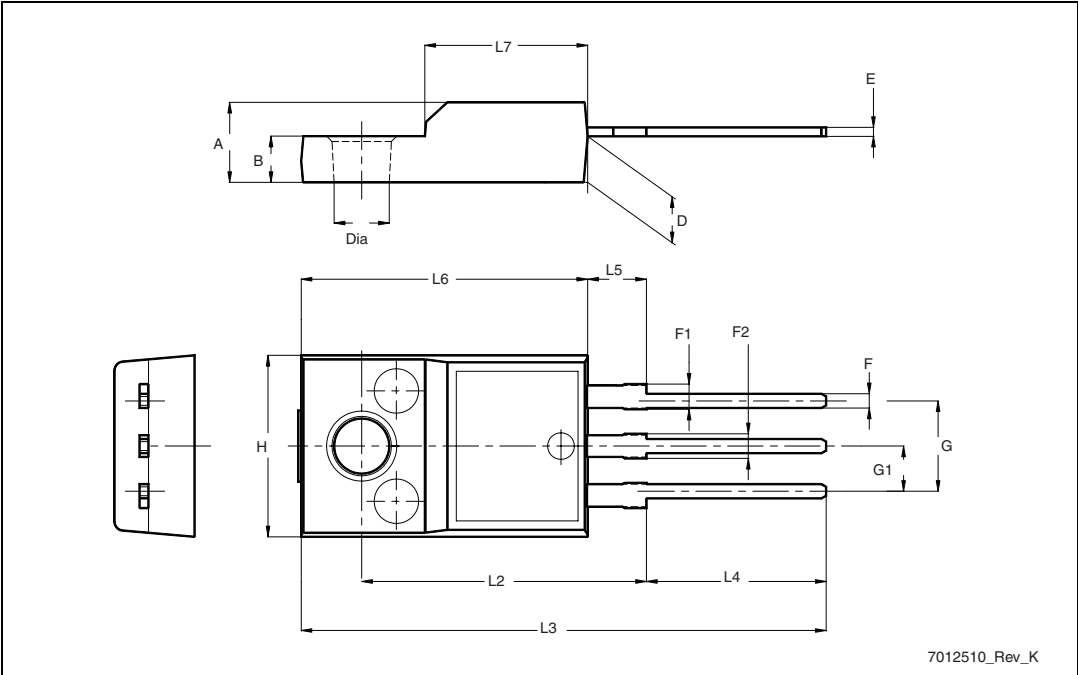


Table 10. D²PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 25. D²PAK footprint^(a)

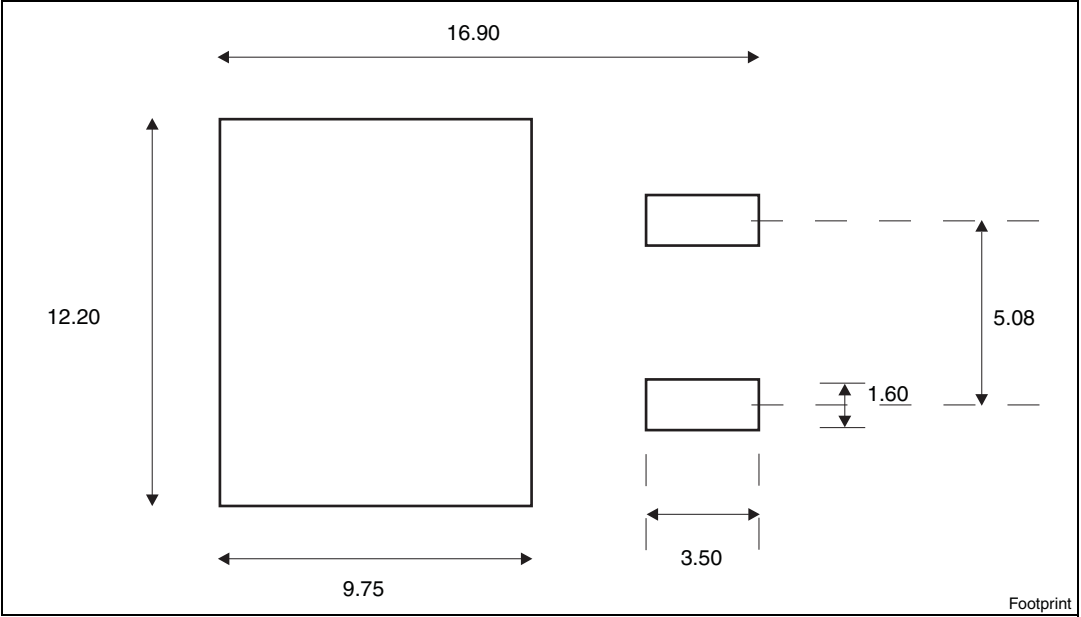
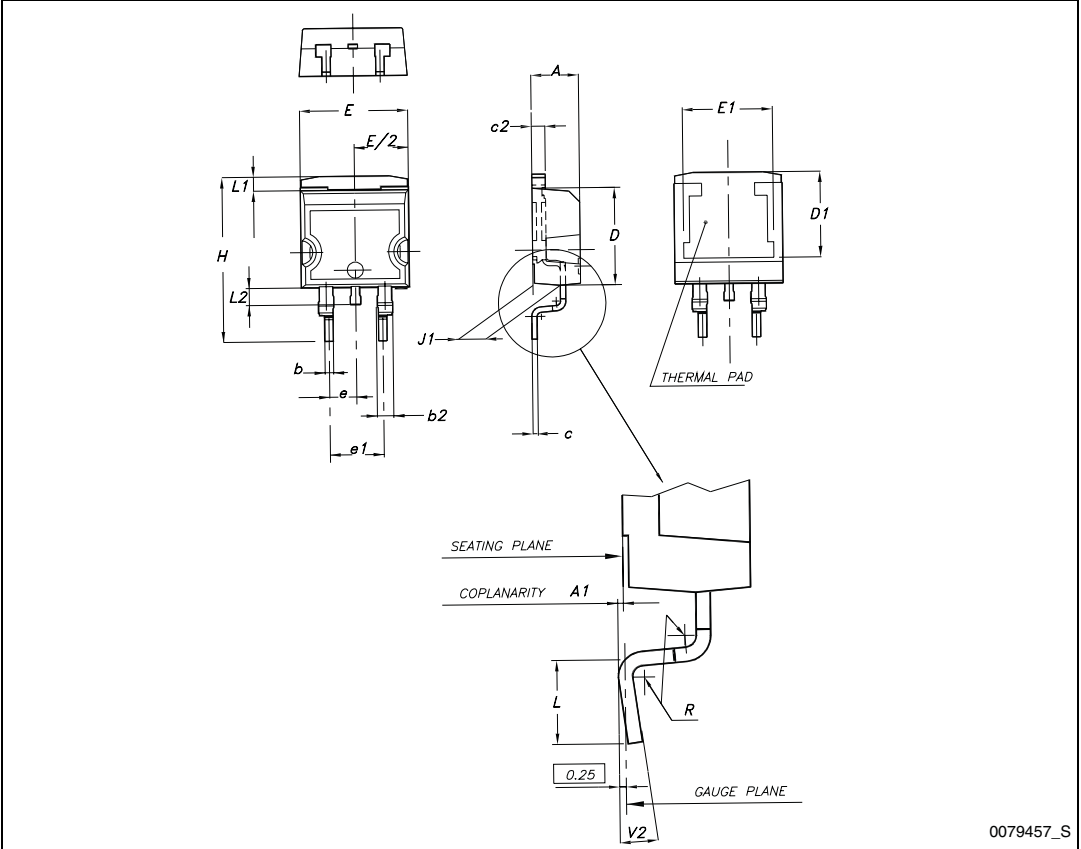


Figure 26. D²PAK (TO-263) drawing



a. All dimension are in millimeters

Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 27. TO-220 type A drawing

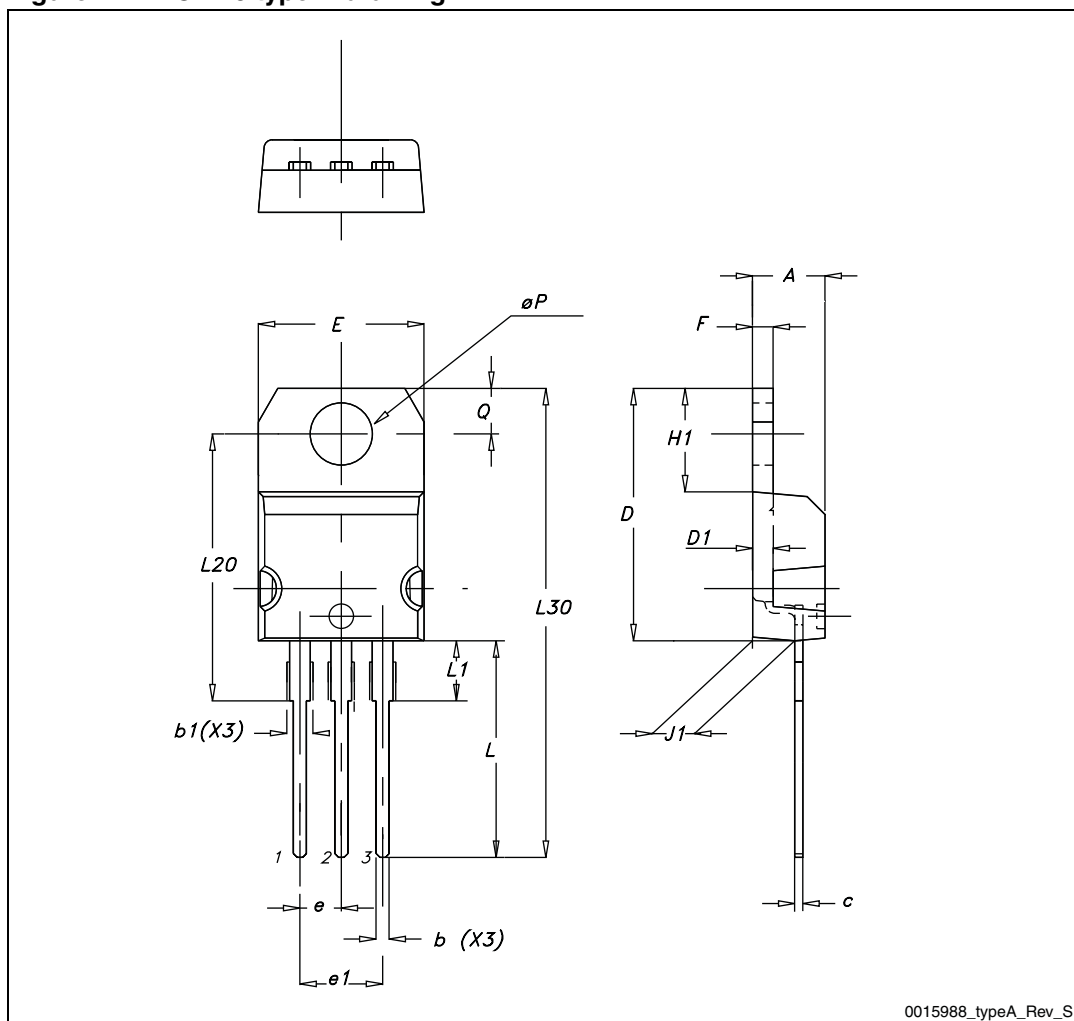
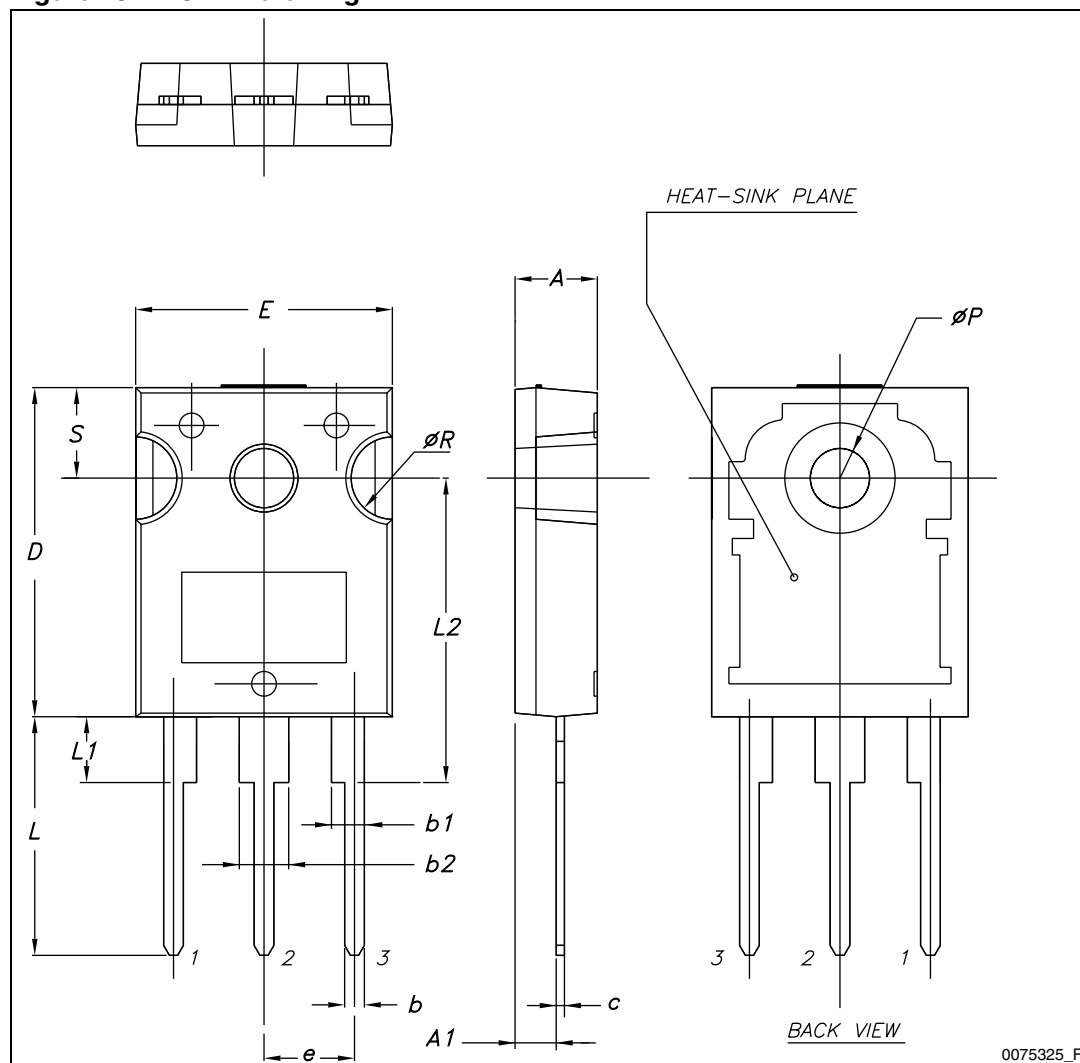


Table 12. TO-247 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e		5.45	
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S		5.50	

Figure 28. TO-247 drawing



5 Packaging mechanical data

Table 13. D²PAK (TO-263) tape and reel mechanical data

Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base qty		1000
P2	1.9	2.1	Bulk qty		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 29. Tape

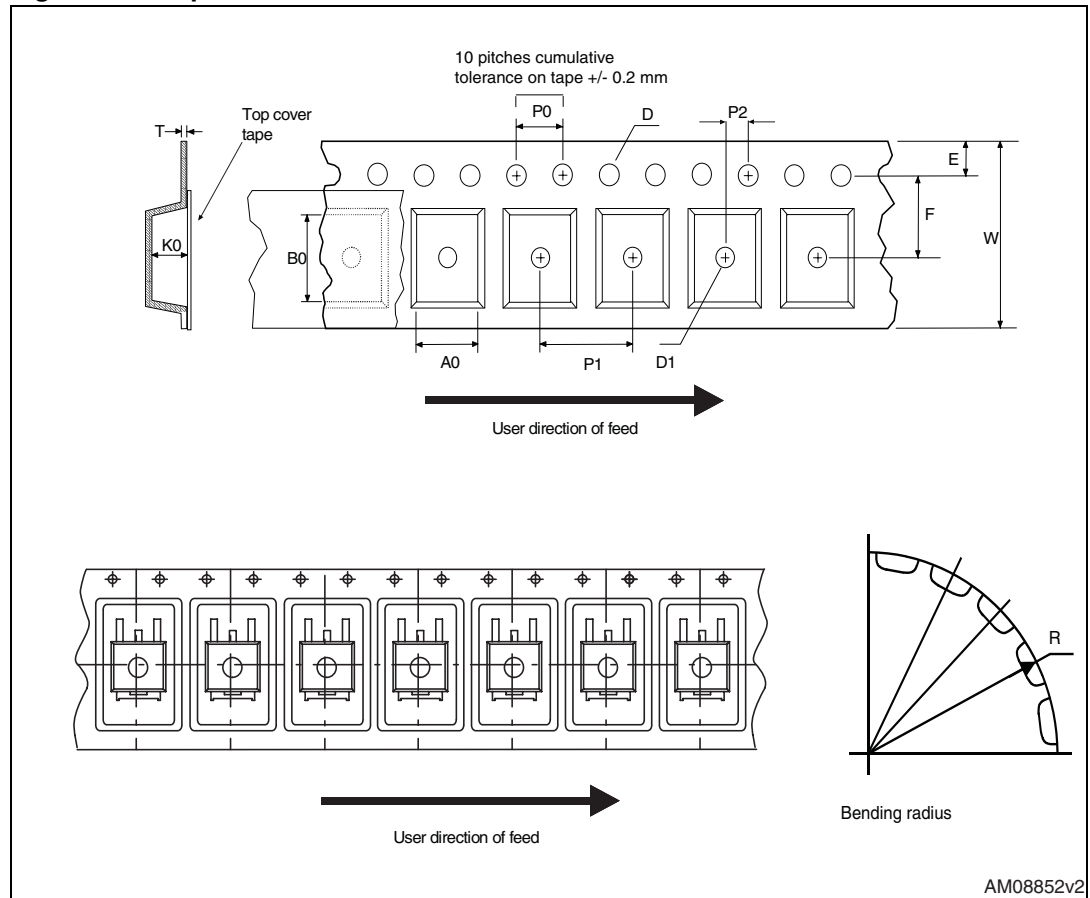
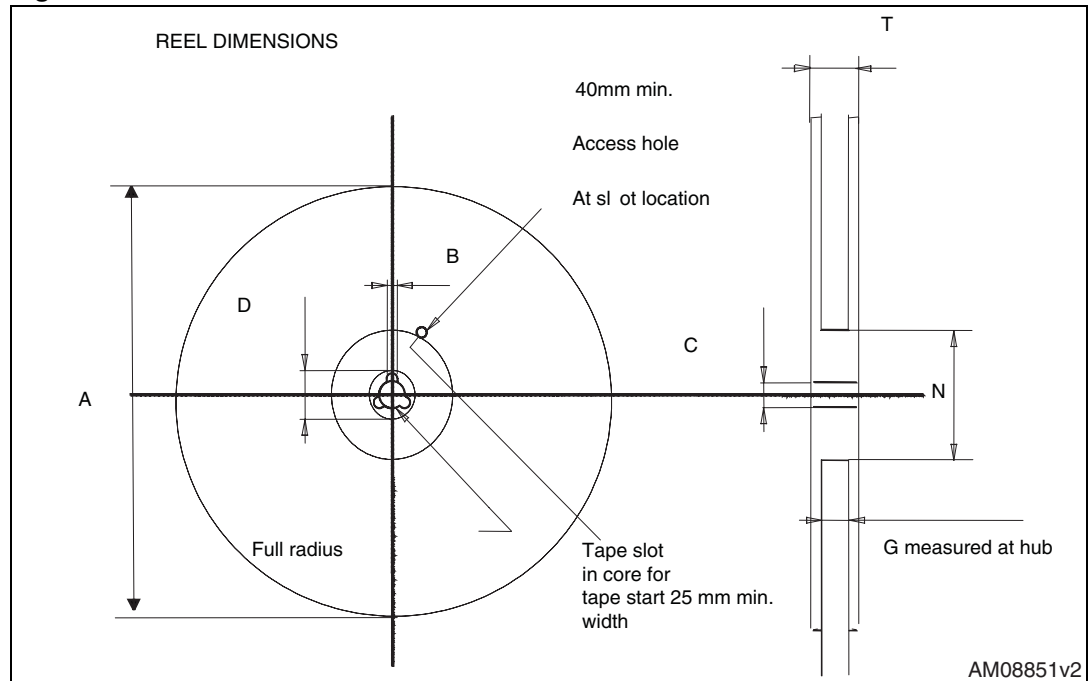


Figure 30. Reel



6 Revision history

Table 14. Document revision history

Date	Revision	Changes
19-Jul-2010	1	First release.
27-Jun-2011	2	– Updated Table 6: Dynamic. – Updated Section 2.1: Electrical characteristics (curves).

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2011 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com